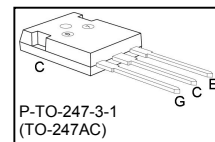
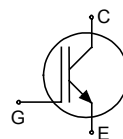


## Low Loss IGBT in Trench and Fieldstop technology

- Best in class TO247
- Short circuit withstand time – 10μs
- Designed for :
  - Frequency Converters
  - Uninterrupted Power Supply
- Trench and Fieldstop technology for 1200 V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
- NPT technology offers easy parallel switching capability due to positive temperature coefficient in  $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Package	Ordering Code
IGW60T120	1200V	60A	1.9V	150°C	TO-247AC	Q67040-S4521

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1200	V
DC collector current	$I_C$		A
$T_C = 25^\circ C$		100	
$T_C = 90^\circ C$		60	
Pulsed collector current, $t_p$ limited by $T_{j,max}$	$I_{C,puls}$	150	
Turn off safe operating area $V_{CE} \leq 1200V, T_j \leq 150^\circ C$	-	150	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Short circuit withstand time <sup>1)</sup> $V_{GE} = 15V, V_{CC} \leq 1200V, T_j \leq 150^\circ C$	$t_{SC}$	10	μs
Power dissipation $T_C = 25^\circ C$	$P_{tot}$	375	W
Operating junction temperature	$T_j$	-40...+150	°C
Storage temperature	$T_{stg}$	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

### Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		0.33	K/W
Thermal resistance, junction – ambient	$R_{thJA}$	TO-247AC	40	

### Electrical Characteristic, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=3.0mA$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=60A$ $T_j=25\text{ }^\circ\text{C}$ $T_j=125\text{ }^\circ\text{C}$ $T_j=150\text{ }^\circ\text{C}$	-	1.9	2.4	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=2.0mA, V_{CE}=V_{GE}$	5.0	5.8	6.5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25\text{ }^\circ\text{C}$ $T_j=150\text{ }^\circ\text{C}$	-	-	0.6	mA
			-	-	6.0	
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	600	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=60A$	-	30	-	S
Integrated gate resistor	$R_{Gint}$			4		$\Omega$

**Dynamic Characteristic**

Input capacitance	$C_{iss}$	$V_{CE}=25V,$	-	3700	-	pF
Output capacitance	$C_{oss}$	$V_{GE}=0V,$	-	180	-	
Reverse transfer capacitance	$C_{rss}$	$f=1MHz$	-	150	-	
Gate charge	$Q_{Gate}$	$V_{CC}=960V, I_C=60A$ $V_{GE}=15V$	-	280	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$	TO-247AC	-	-	13	nH
Short circuit collector current <sup>1)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC} \leq 10\mu s$ $V_{CC} = 600V,$ $T_j = 25^\circ C$	-	300	-	A

**Switching Characteristic, Inductive Load, at  $T_j=25^\circ C$**

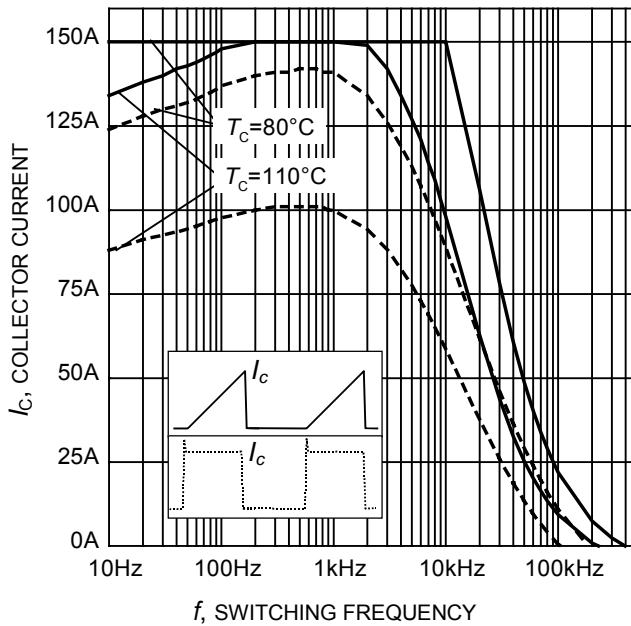
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ C,$ $V_{CC}=600V, I_C=60A,$ $V_{GE}=0/15V,$ $R_G=10\Omega,$ $L_{\sigma}^{(2)}=180nH,$ $C_{\sigma}^{(2)}=39pF$ Energy losses include "tail" and diode reverse recovery.	-	50	-	ns
Rise time	$t_r$		-	44	-	
Turn-off delay time	$t_{d(off)}$		-	480	-	
Fall time	$t_f$		-	80	-	
Turn-on energy	$E_{on}$		-	4.3	-	mJ
Turn-off energy	$E_{off}$		-	5.2	-	
Total switching energy	$E_{ts}$		-	9.5	-	

**Switching Characteristic, Inductive Load, at  $T_j=150^\circ C$**

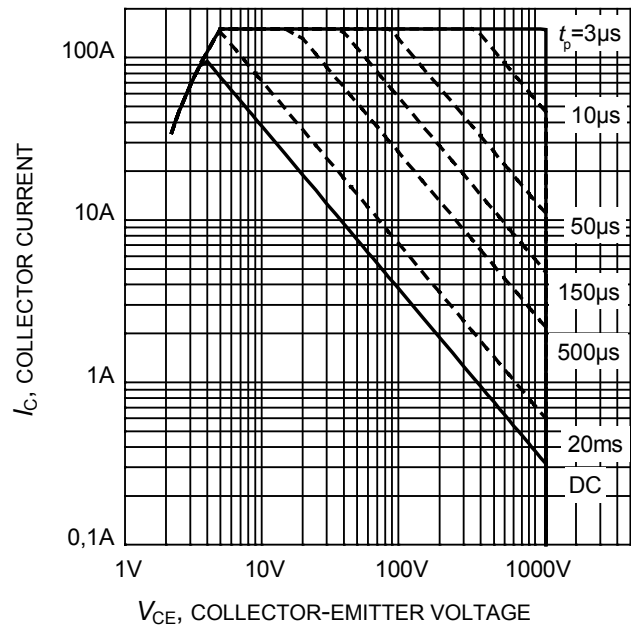
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ C$ $V_{CC}=600V, I_C=60A,$ $V_{GE}=0/15V,$ $R_G=10\Omega,$ $L_{\sigma}^{(2)}=180nH,$ $C_{\sigma}^{(2)}=39pF$ Energy losses include "tail" and diode reverse recovery.	-	50	-	ns
Rise time	$t_r$		-	45	-	
Turn-off delay time	$t_{d(off)}$		-	600	-	
Fall time	$t_f$		-	130	-	
Turn-on energy	$E_{on}$		-	6.4	-	mJ
Turn-off energy	$E_{off}$		-	9.4	-	
Total switching energy	$E_{ts}$		-	15.8	-	

<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

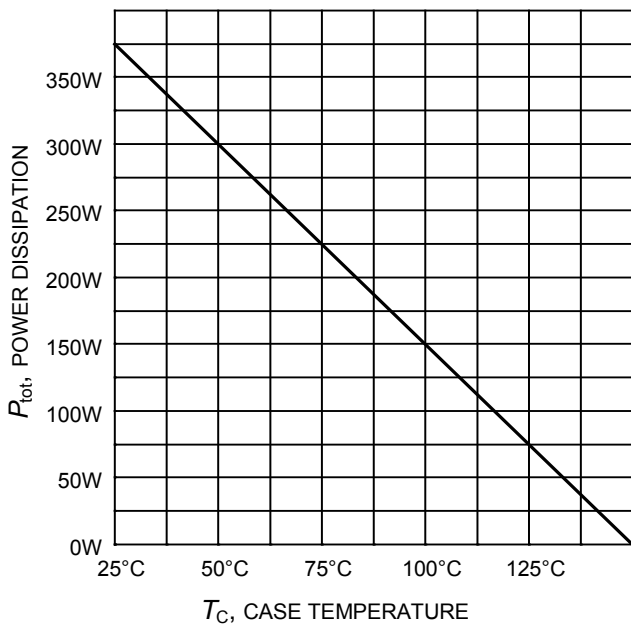
<sup>2)</sup> Leakage inductance  $L_{\sigma}$  and Stray capacity  $C_{\sigma}$  due to dynamic test circuit in Figure E.



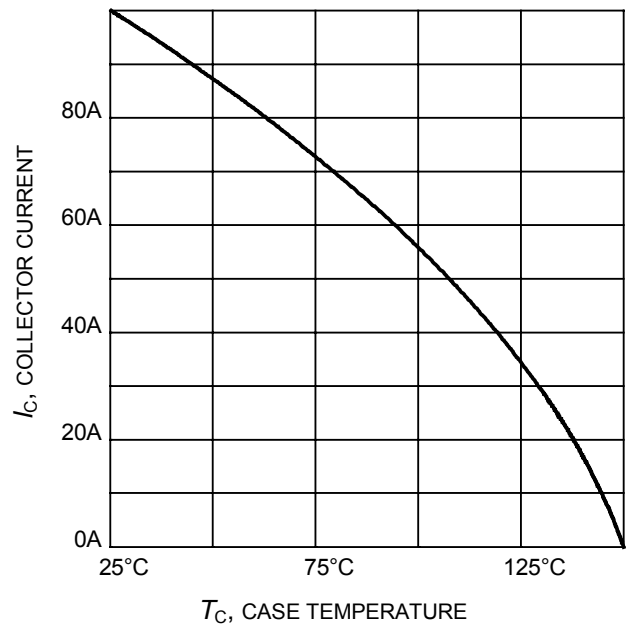
**Figure 1. Collector current as a function of switching frequency**  
 ( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 600\text{V}$ ,  $V_{GE} = 0/+15\text{V}$ ,  $R_G = 10\Omega$ )



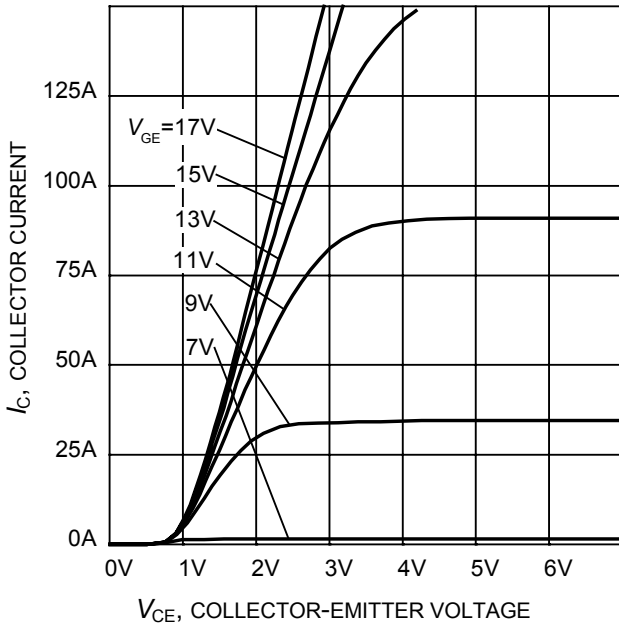
**Figure 2. Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 150^\circ\text{C}$ ;  $V_{GE} = 15\text{V}$ )



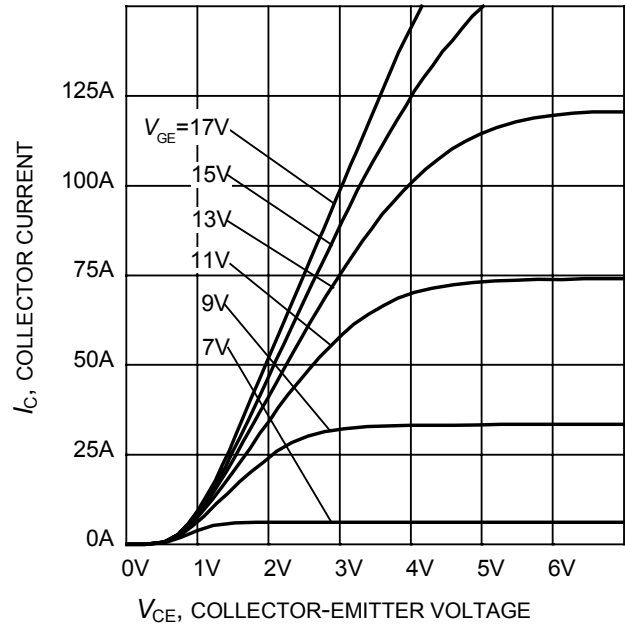
**Figure 3. Power dissipation as a function of case temperature**  
 ( $T_j \leq 150^\circ\text{C}$ )



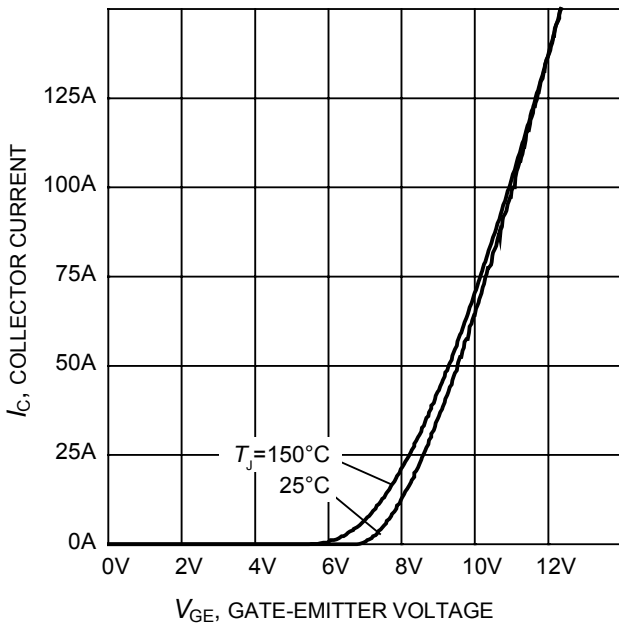
**Figure 4. Collector current as a function of case temperature**  
 ( $V_{GE} \geq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )



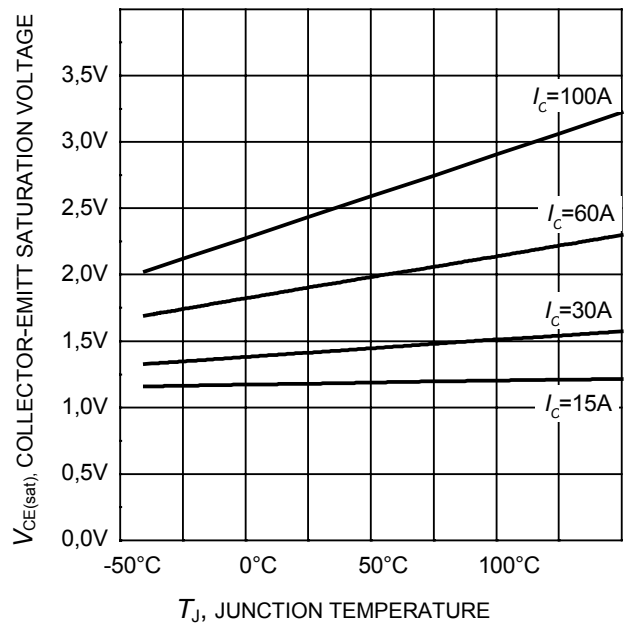
**Figure 5. Typical output characteristic**  
( $T_j = 25^\circ\text{C}$ )



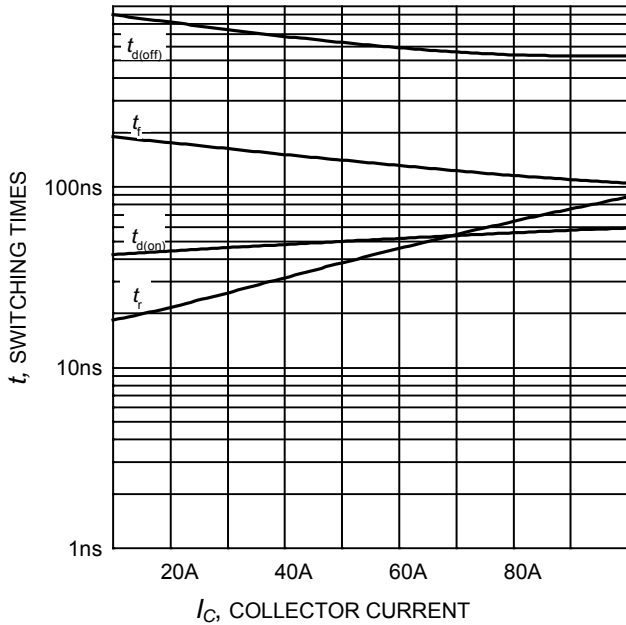
**Figure 6. Typical output characteristic**  
( $T_j = 150^\circ\text{C}$ )



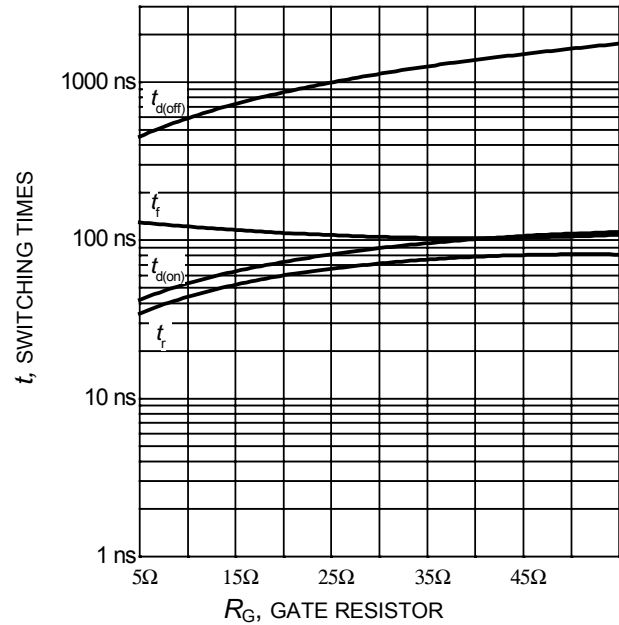
**Figure 7. Typical transfer characteristic**  
( $V_{CE} = 20\text{V}$ )



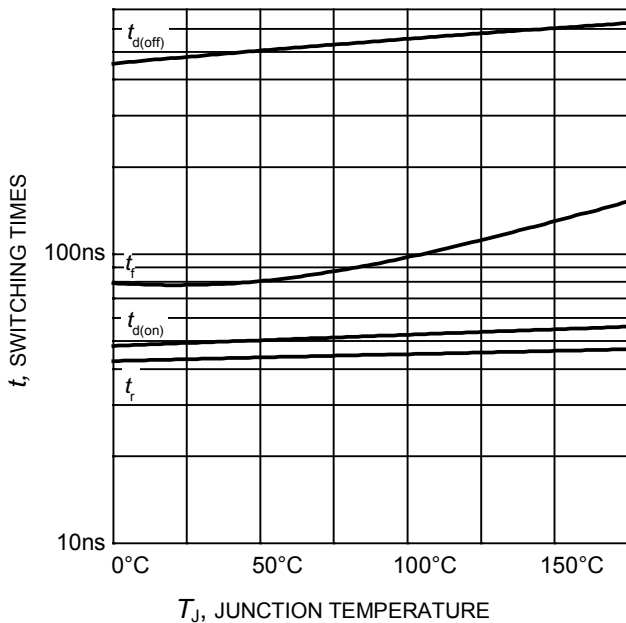
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



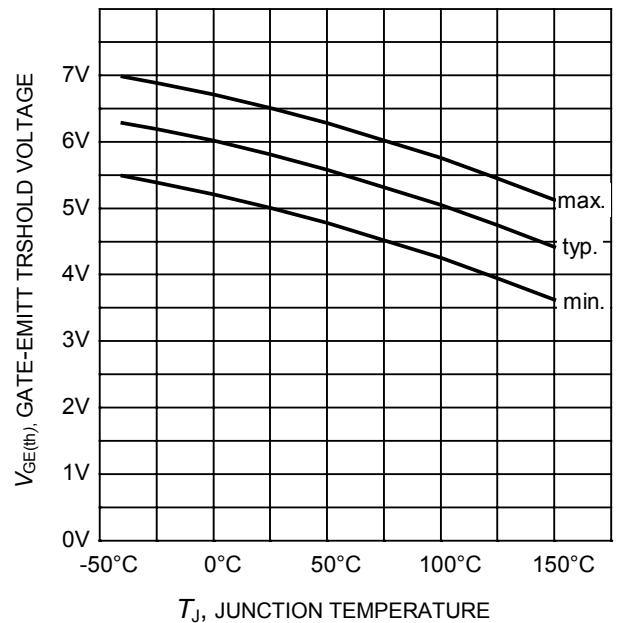
**Figure 9. Typical switching times as a function of collector current**  
(inductive load,  $T_J=150^{\circ}\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



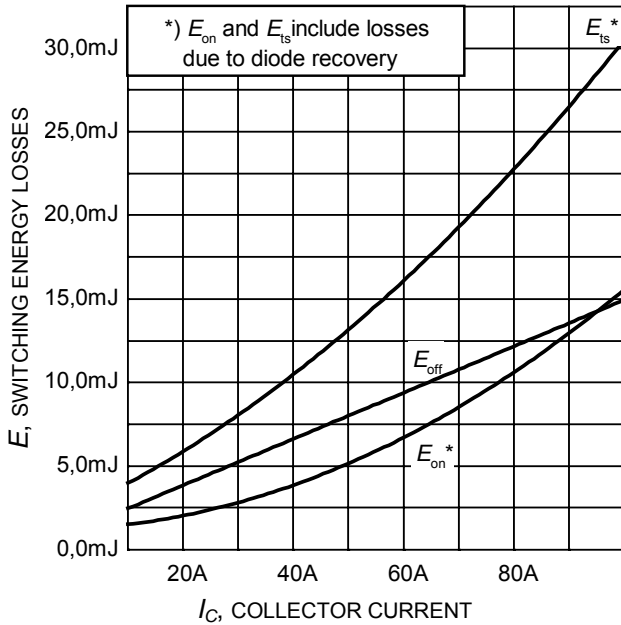
**Figure 10. Typical switching times as a function of gate resistor**  
(inductive load,  $T_J=150^{\circ}\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=60\text{A}$ , Dynamic test circuit in Figure E)



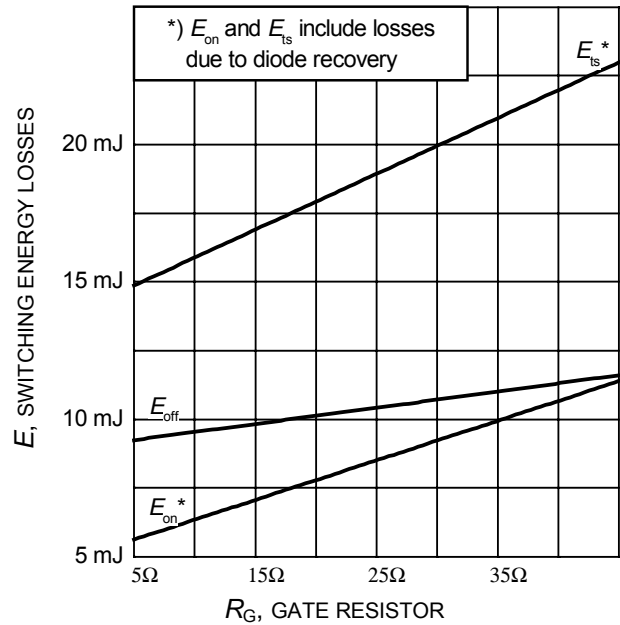
**Figure 11. Typical switching times as a function of junction temperature**  
(inductive load,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=60\text{A}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



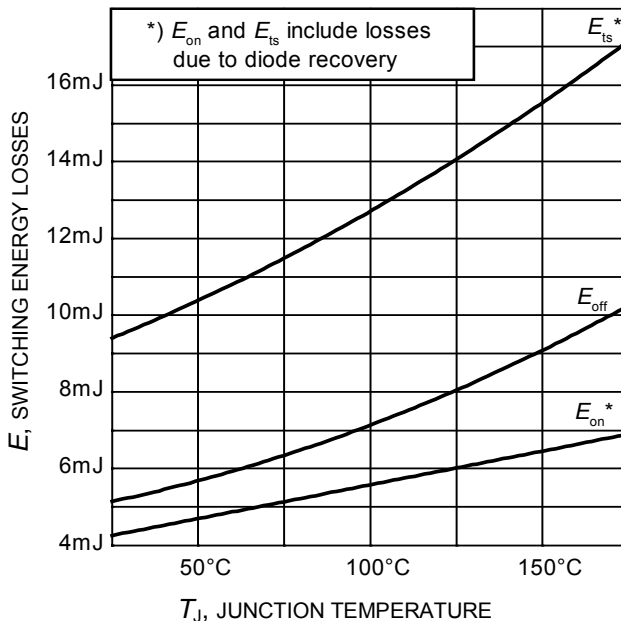
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
( $I_C = 2.0\text{mA}$ )



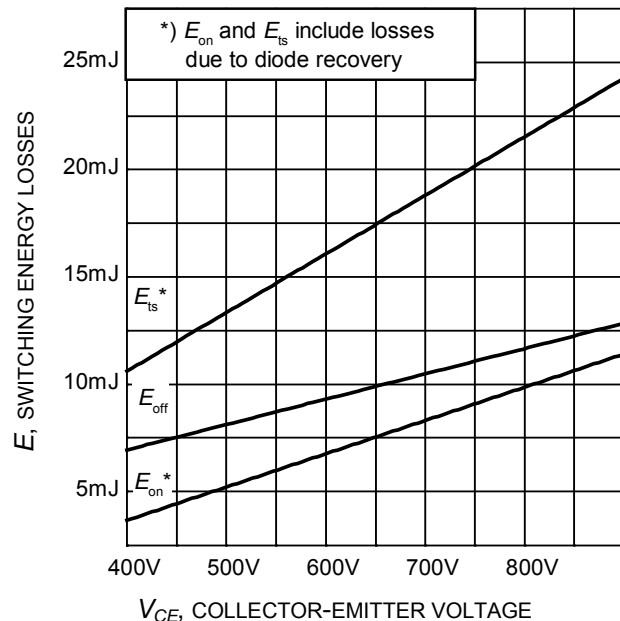
**Figure 13. Typical switching energy losses as a function of collector current**  
 (inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



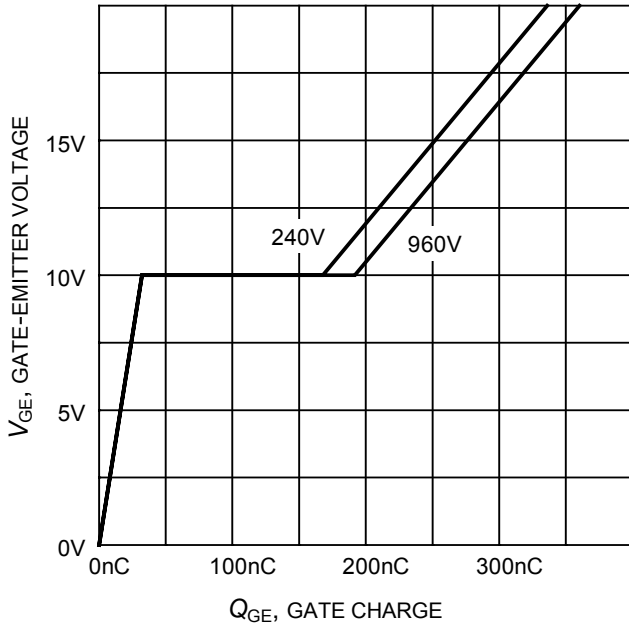
**Figure 14. Typical switching energy losses as a function of gate resistor**  
 (inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=60\text{A}$ , Dynamic test circuit in Figure E)



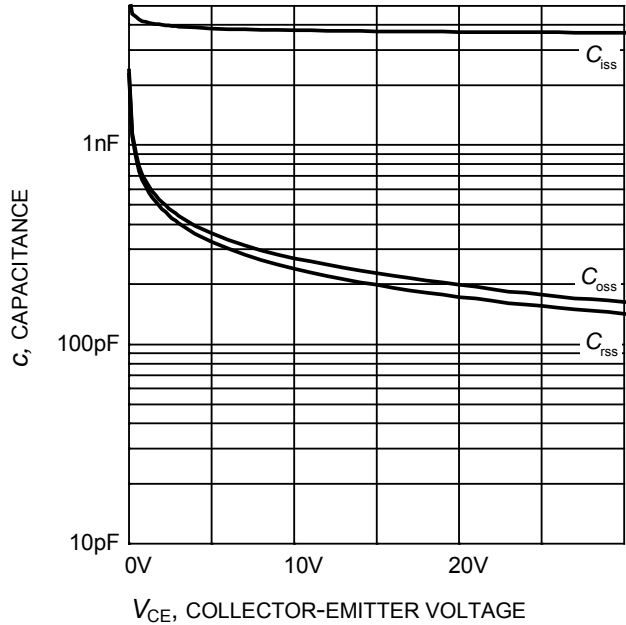
**Figure 15. Typical switching energy losses as a function of junction temperature**  
 (inductive load,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=60\text{A}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



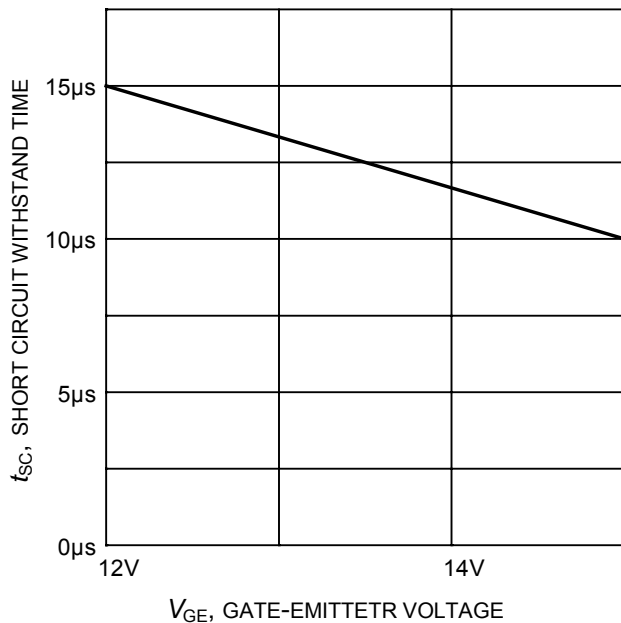
**Figure 16. Typical switching energy losses as a function of collector emitter voltage**  
 (inductive load,  $T_J=150^\circ\text{C}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=60\text{A}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



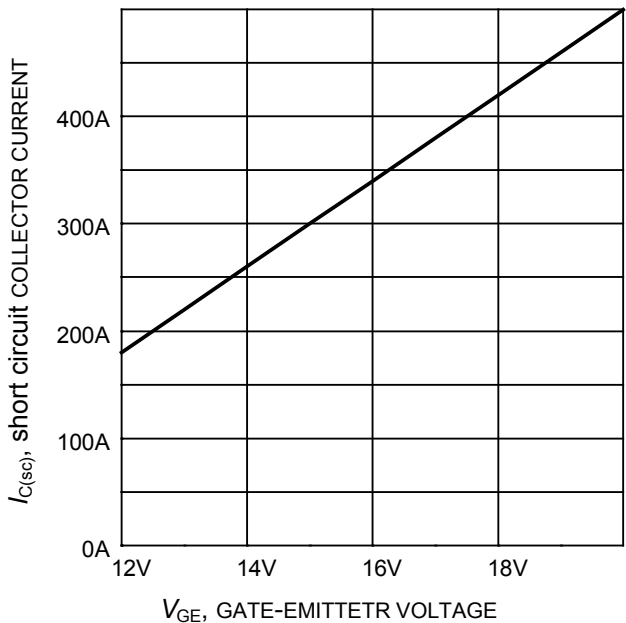
**Figure 17. Typical gate charge**  
( $I_C=60\text{ A}$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0\text{V}$ ,  $f = 1\text{ MHz}$ )

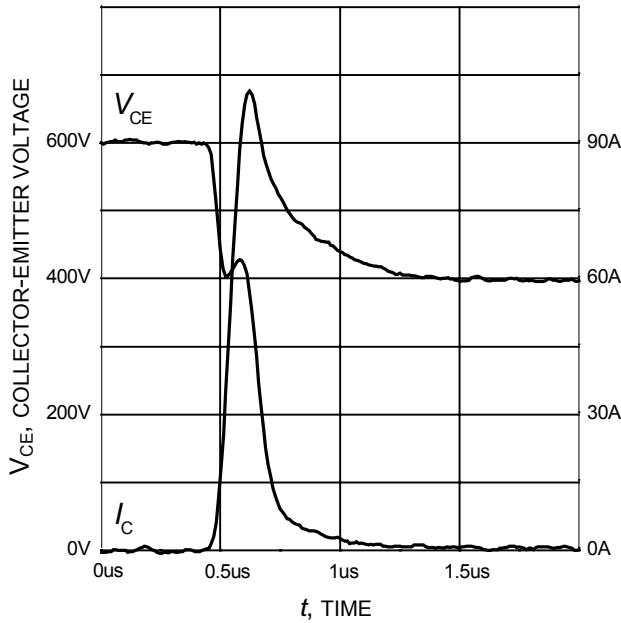


**Figure 19. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE}=600\text{V}$ , start at  $T_j=25^\circ\text{C}$ )

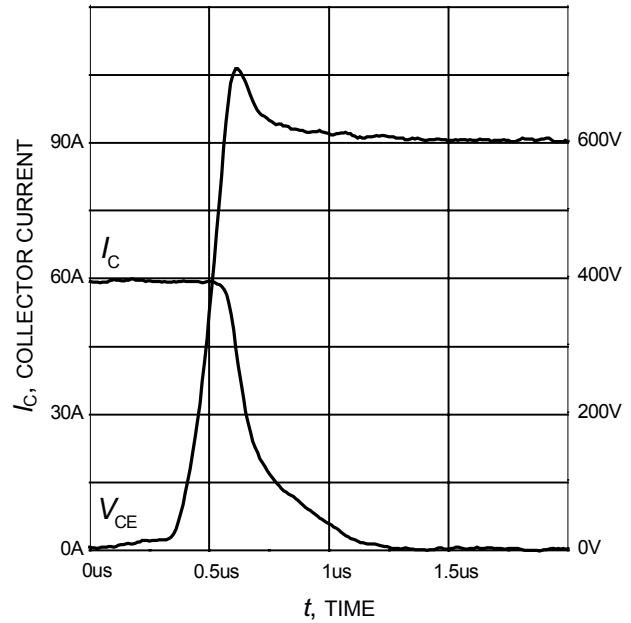


**Figure 20. Typical short circuit collector current as a function of gate-emitter voltage**  
( $V_{CE} \leq 600\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )

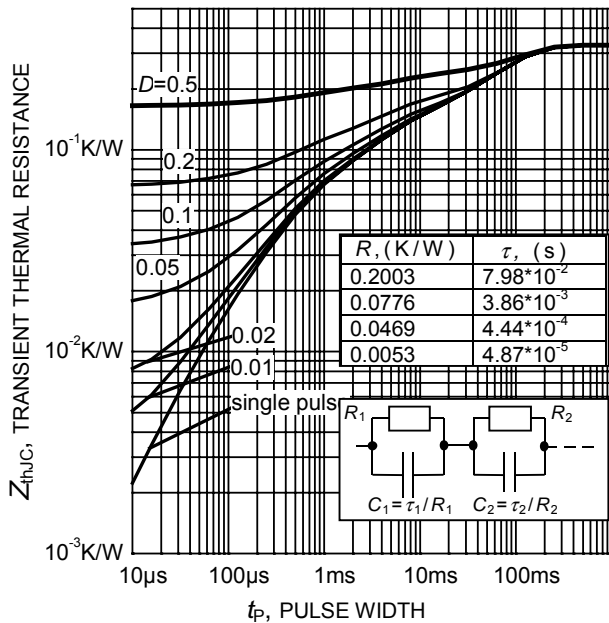




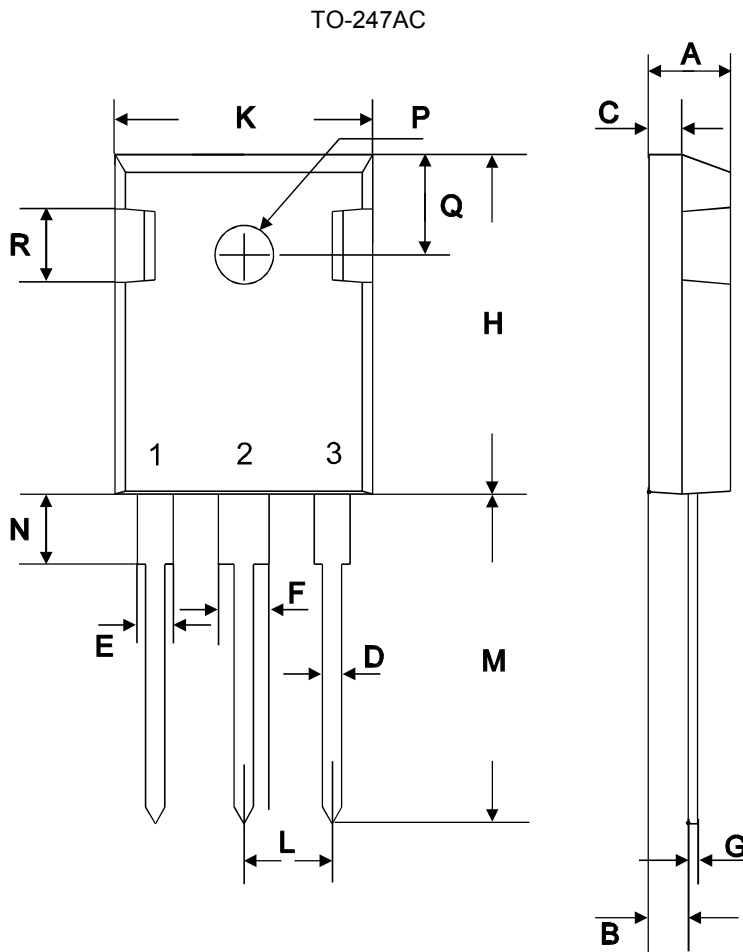
**Figure 21. Typical turn on behavior**  
 ( $V_{GE}=0/15V$ ,  $R_G=10\Omega$ ,  $T_j = 150^\circ C$ ,  
 Dynamic test circuit in Figure E)



**Figure 22. Typical turn off behavior**  
 ( $V_{GE}=15/0V$ ,  $R_G=10\Omega$ ,  $T_j = 150^\circ C$ ,  
 Dynamic test circuit in Figure E)



**Figure 23. IGBT transient thermal resistance**  
 ( $D = t_p / T$ )



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	4.78	5.28	0.1882	0.2079
B	2.29	2.51	0.0902	0.0988
C	1.78	2.29	0.0701	0.0902
D	1.09	1.32	0.0429	0.0520
E	1.73	2.06	0.0681	0.0811
F	2.67	3.18	0.1051	0.1252
G	0.76 max		0.0299 max	
H	20.80	21.16	0.8189	0.8331
K	15.65	16.15	0.6161	0.6358
L	5.21	5.72	0.2051	0.2252
M	19.81	20.68	0.7799	0.8142
N	3.560	4.930	0.1402	0.1941
∅P	3.61		0.1421	
Q	6.12	6.22	0.2409	0.2449

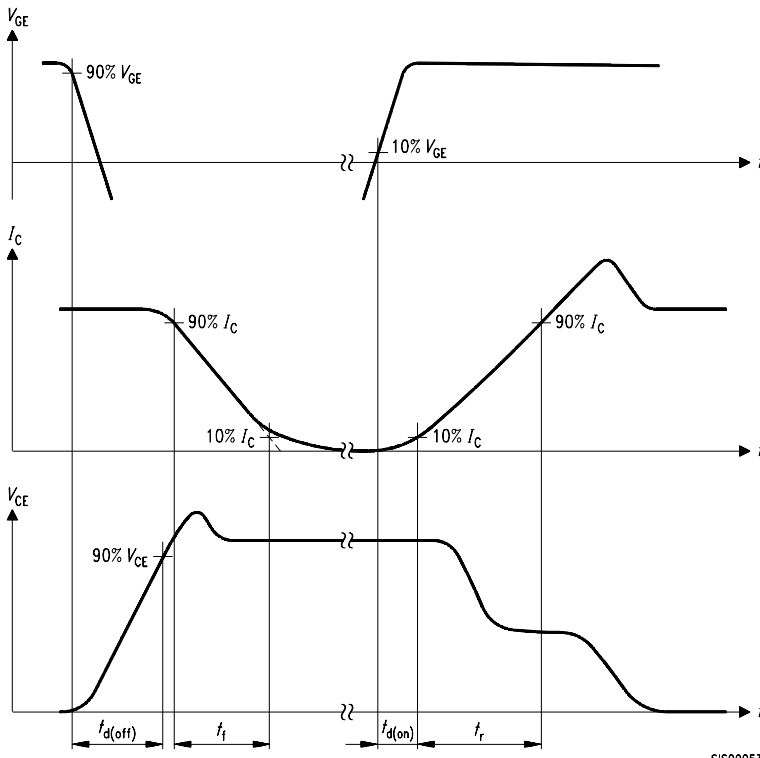


Figure A. Definition of switching times

SIS00053

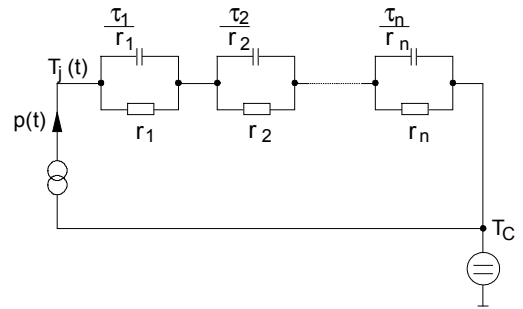


Figure D. Thermal equivalent circuit

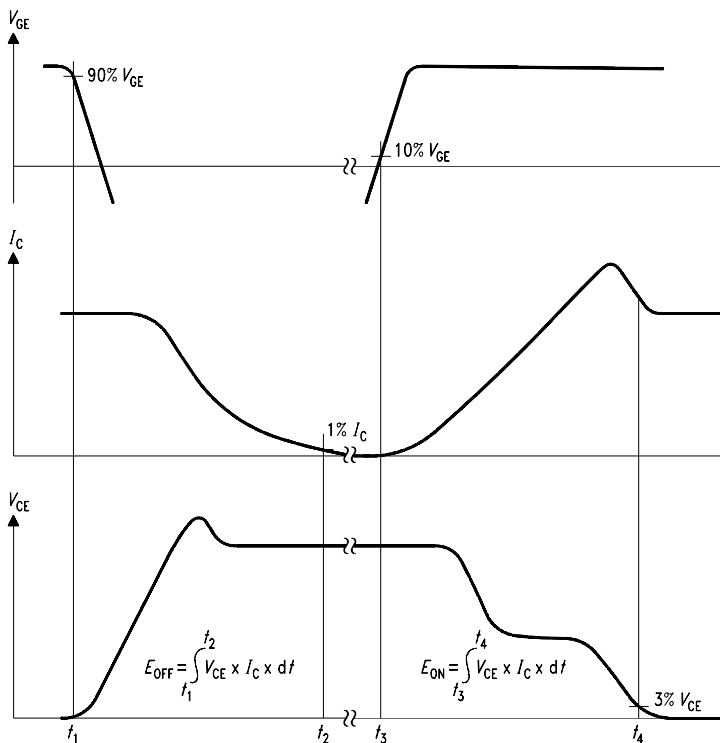


Figure B. Definition of switching losses

SIS

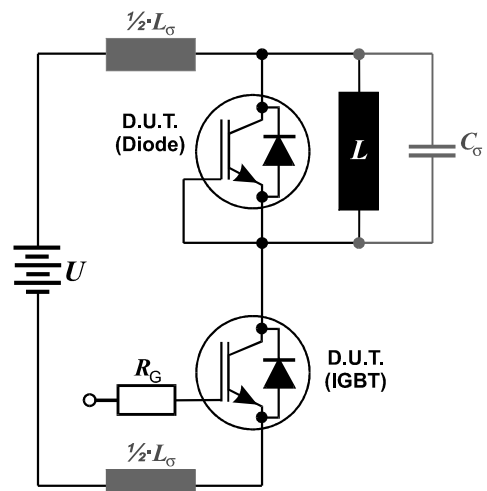


Figure E. Dynamic test circuit  
Leakage inductance  $L_{\sigma} = 180\text{nH}$   
and Stray capacity  $C_{\sigma} = 39\text{pF}$ .

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